

January 1998

6A, 400V - 600V Hyperfast Dual Diodes

Features

- Hyperfast with Soft Recovery<30ns
- Operating Temperature175°C
- Reverse Voltage Up To600V
- Avalanche Energy Rated
- Planar Construction
- Related Literature
 - TB334 "Guidelines for Soldering Surface Mount Components to PC Boards"

Applications

- Switching Power Supplies
- Power Switching Circuits
- General Purpose

Ordering Information

| PART NUMBER | PACKAGE | BRAND |
|-------------|----------|----------|
| RHRP640CC | TO-220AB | RHRP640C |
| RHRP650CC | TO-220AB | RHRP650C |
| RHRP660CC | TO-220AB | RHRP660C |

NOTE: When ordering, use the entire part number.

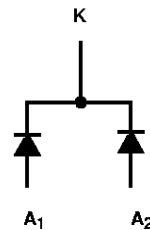
Description

RHRP640CC, RHRP650CC and RHRP660CC are hyperfast dual diodes with soft recovery characteristics ($t_{rr} < 30\text{ns}$). They have half the recovery time of ultrafast diodes and are silicon nitride passivated ion-implanted hepaticas planar construction.

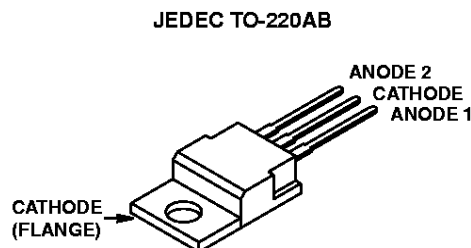
These devices are intended for use as freewheeling/clamping diodes and rectifiers in a variety of switching power supplies and other power switching applications. Their low stored charge and ultrafast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

Formerly developmental type TA49057.

Symbol



Packaging



RHRP640CC, RHRP650CC, RHRP660CC

Absolute Maximum Ratings (Per Leg) $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

| | | RHRP640CC | RHRP650CC | RHRP660CC | UNITS |
|--|----------------|------------|------------|------------|------------------|
| Peak Repetitive Reverse Voltage | V_{RRM} | 400 | 500 | 600 | V |
| Working Peak Reverse Voltage | V_{RWM} | 400 | 500 | 600 | V |
| DC Blocking Voltage | V_R | 400 | 500 | 600 | V |
| Average Rectified Forward Current | $I_{F(AV)}$ | 6 | 6 | 6 | A |
| $T_C = 152^\circ\text{C}$ | | | | | |
| Repetitive Peak Surge Current | I_{FSM} | 12 | 12 | 12 | A |
| Square Wave, 20kHz | | | | | |
| Nonrepetitive Peak Surge Current | I_{FSM} | 60 | 60 | 60 | A |
| Halfwave, 1 phase, 60Hz | | | | | |
| Maximum Power Dissipation | P_D | 50 | 50 | 50 | W |
| Avalanche Energy (See Figures 10 and 11) | E_{AVL} | 10 | 10 | 10 | mJ |
| Operating and Storage Temperature | T_{STG, T_J} | -65 to 175 | -65 to 175 | -65 to 175 | $^\circ\text{C}$ |
| Maximum Temperature for Soldering | | | | | |
| Leads at 0.063in (1.6mm) from Case for 10s | T_L | 300 | 300 | 300 | $^\circ\text{C}$ |
| Package Body for 10s, see Tech Brief 334 | T_{pkg} | 260 | 260 | 260 | $^\circ\text{C}$ |

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Electrical Specifications (Per Leg) $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

| SYMBOL | TEST CONDITION | RHRP640CC | | | RHRP650CC | | | RHRP660CC | | | UNITS |
|-----------------|--|-----------|-----|-----|-----------|-----|-----|-----------|-----|-----|---------------------------|
| | | MIN | TYP | MAX | MIN | TYP | MAX | MIN | TYP | MAX | |
| V_F | $I_F = 6\text{A}$ | - | - | 2.1 | - | - | 2.1 | - | - | 2.1 | V |
| | $I_F = 6\text{A}, T_C = 150^\circ\text{C}$ | - | - | 1.7 | - | - | 1.7 | - | - | 1.7 | V |
| I_R | $V_R = 400\text{V}$ | - | - | 100 | - | - | - | - | - | - | μA |
| | $V_R = 500\text{V}$ | - | - | - | - | - | 100 | - | - | - | μA |
| | $V_R = 600\text{V}$ | - | - | - | - | - | - | - | - | 100 | μA |
| | $V_R = 400\text{V}, T_C = 150^\circ\text{C}$ | - | - | 500 | - | - | - | - | - | - | μA |
| | $V_R = 500\text{V}, T_C = 150^\circ\text{C}$ | - | - | - | - | - | 500 | - | - | - | μA |
| | $V_R = 600\text{V}, T_C = 150^\circ\text{C}$ | - | - | - | - | - | - | - | - | 500 | μA |
| t_{rr} | $I_F = 1\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$ | - | - | 30 | - | - | 30 | - | - | 30 | ns |
| | $I_F = 6\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$ | - | - | 35 | - | - | 35 | - | - | 35 | ns |
| t_a | $I_F = 6\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$ | - | 16 | - | - | 16 | - | - | 16 | - | ns |
| t_b | $I_F = 6\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$ | - | 8.5 | - | - | 8.5 | - | - | 8.5 | - | ns |
| Q_{RR} | $I_F = 6\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$ | - | 45 | - | - | 45 | - | - | 45 | - | nC |
| C_J | $V_R = 10\text{V}, I_F = 0\text{A}$ | - | 20 | - | - | 20 | - | - | 20 | - | pF |
| $R_{\theta JC}$ | | - | - | 3 | - | - | 3 | - | - | 3 | $^\circ\text{C}/\text{W}$ |

DEFINITIONS

V_F = Instantaneous forward voltage ($p_w = 300\mu\text{s}$, $D = 2\%$).

I_R = Instantaneous reverse current.

t_{rr} = Reverse recovery time (See Figure 9), summation of $t_a + t_b$.

t_a = Time to reach peak reverse current (See Figure 9).

t_b = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 9).

Q_{RR} = Reverse recovery charge.

C_J = Junction Capacitance.

$R_{\theta JC}$ = Thermal resistance junction to case.

p_w = pulse width.

D = duty cycle.

Typical Performance Curves

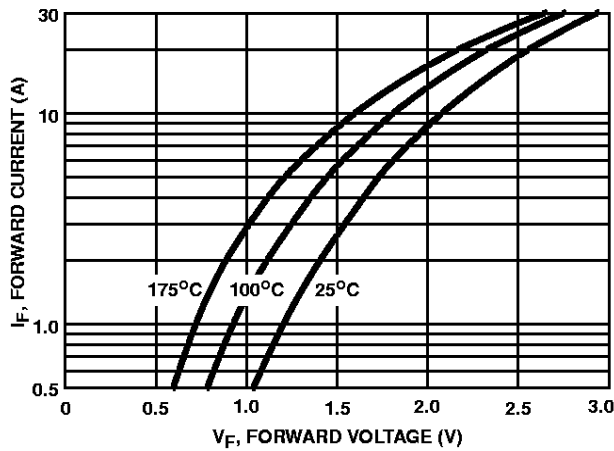


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

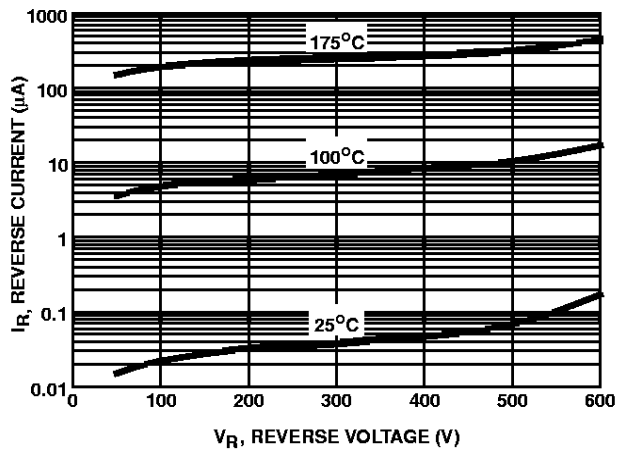


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

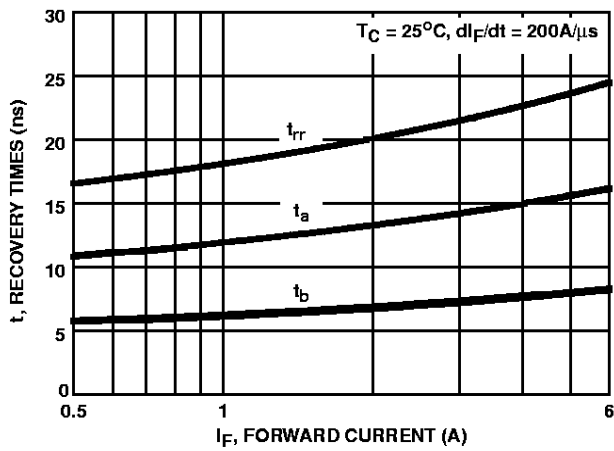


FIGURE 3. t_{rr} , t_a AND t_b CURVES vs FORWARD CURRENT

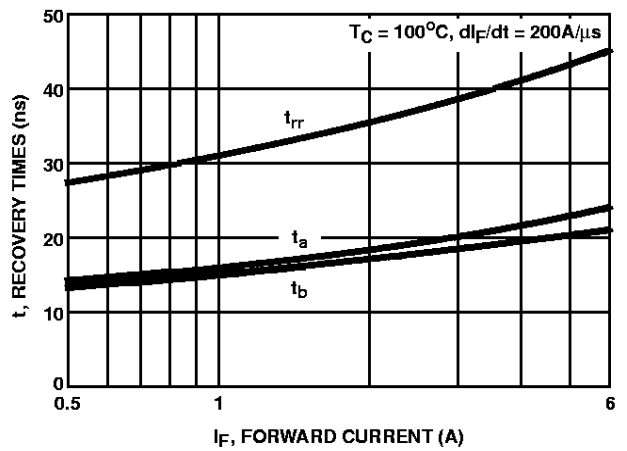


FIGURE 4. t_{rr} , t_a AND t_b CURVES vs FORWARD CURRENT

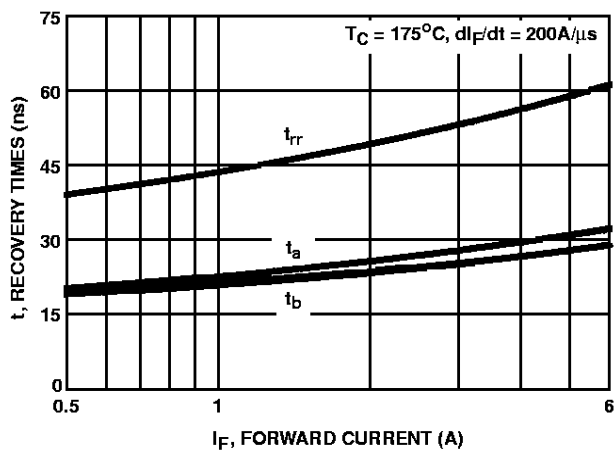


FIGURE 5. t_{rr} , t_a AND t_b CURVES vs FORWARD CURRENT

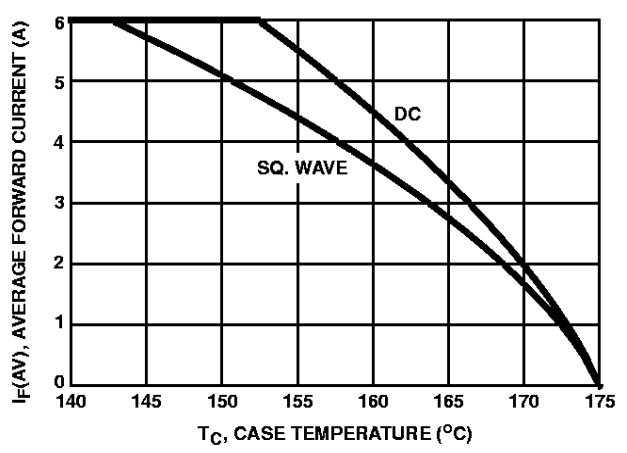


FIGURE 6. CURRENT DERATING CURVE